

Silicon NPN Power Transistors

2N5671 2N5672

DESCRIPTION

- With TO-3 package
- High current ,high speed

APPLICATIONS

- Intended for high current and fast switching industrial applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

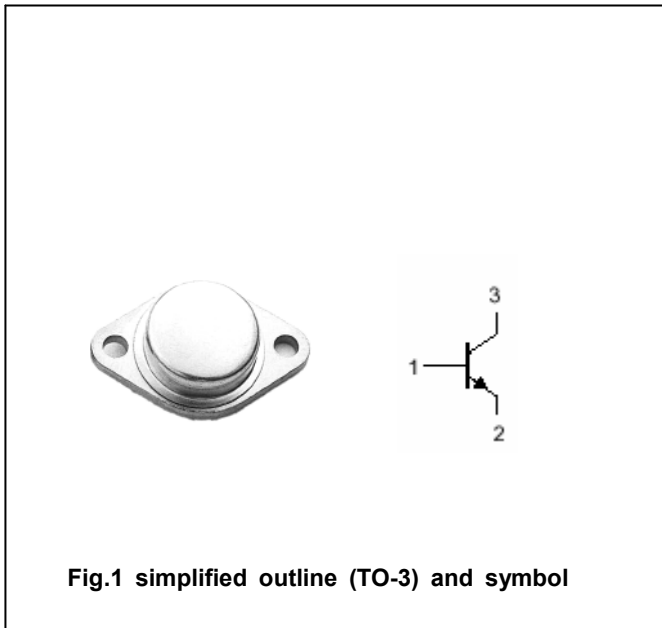


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5671	120	V
		2N5672	150	
V _{CEO}	Collector-emitter voltage	2N5671	90	V
		2N5672	120	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		30	A
I _B	Base current		10	A
P _D	Total Power Dissipation	T _C =25□	140	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.25	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5671	I _C =0.2A ; I _B =0	90			V
		2N5672		120			
V _{CEsat}	Collector-emitter saturation voltage		I _C =15A ; I _B =1.2A			0.75	V
V _{BEsat}	Base-emitter saturation voltage		I _C =15A ; I _B =1.2A			1.5	V
V _{BE}	Base-emitter on voltage		I _C =15A ; V _{CE} =5V			1.6	V
I _{CEO}	Collector cut-off current		V _{CE} =80V ; I _B =0			10	mA
I _{CEV}	Collector cut-off current	2N5671	V _{CE} =110V ; V _{BE(off)} =1.5V			12	mA
		2N5672	V _{CE} =135V ; V _{BE(off)} =1.5V			10	
		2N5671	V _{CE} =100V ; V _{BE(off)} =1.5V ; T _C =150°C			15	
		2N5672	V _{CE} =100V ; V _{BE(off)} =1.5V ; T _C =150°C			10	
I _{EBO}	Emitter cut-off current		V _{EB} =7V ; I _C =0			10	mA
h _{FE-1}	DC current gain		I _C =15A ; V _{CE} =2V	20		100	
h _{FE-2}	DC current gain		I _C =20A ; V _{CE} =5V	20			
f _T	Transistion frequency		I _C =2A ; V _{CE} =10V ; f=1MHz	40			MHz

Switching times

t _{on}	Turn-on time	I _C =15A ; I _{B1} =- I _{B2} =1.2A V _{CC} =30V ; t _p =0.1ms			0.5	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.5	μs

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)